

Time of Flight Mass Spectrometry ToF-SIMS

Overview

TOF-SIMS is a very sensitive surface analytical technique. It provides detailed elemental and molecular information about surfaces, thin layers, interfaces, and full three-dimensional analysis of the samples. ToF-SIMS technique is used in different areas including semiconductors, polymers, paint, coatings, glass ceramic, metals biomaterials, and pharmaceuticals. The TOF.SIMS 5 is the high-end TOF-SIMS instrument developed over the last 20 years. Its design guarantees optimum performance in all fields of SIMS applications.



Unique features of the TOF.SIMS 5 are:

- Ultra high sensitivity for molecular species by optimised cluster ion sources
- Outstanding performance for low energy depth profiling
- Sophisticated software for ease of operation and data handling
- Modular construction for configuration and upgrade flexibility
- Ergonomic design with compact footprint

A self-adjusting charge compensation system using a low energy electron flood gun synchronized with ion gun pulsing to neutralize the positive charge after each ion pulse. A 30 keV, three-lens BiMn cluster ion gun. This cluster Liquid Metal ion Gun (LMIG) is ideally suited for high lateral resolution

Technical Details

A two meter reflectron type TOF analyzer with first order energy focusing, an Einzel lens for secondary ion beam transportation, a beam deflector for alignment and dynamic emittance matching, secondary ion beam blanking allowing for repetition rates up to 50 kHz, 10 kV post-acceleration optics, a combined microchannel plate (MCP), scintillator and photomultiplier ion detector, and

a multi-stop time-to-digital converter (TDC) with 50 ps time resolution.

A rapid 100-mm-sample introduction system and two multiple sample holders with rear mounting for samples up to 8 mm thick and top mounting for samples up to 20 mm thick. Full access to all sample surfaces by movement of the microanalysis and imaging as well as high mass resolution surface spectroscopy.

A high current ion optical column (dual source column) to which two ion sources, an electron impact ion source (EI SOURCE) and a thermal ionization Cesium ion source are fitted. This column is used for ultra-low energy sputtering in dual beam depth profiling.

Example Outputs





A motorized five-axes UHV sample stage with large travel (X = 90 mm, Y = 125 mm, Z = 25 mm, tilt = -15° to +45°, and endless rotation).

Illustrative examples of work undertaken at the Bernal Institute: Dual beam depth profiling of the prototype solar cell.



www.bernalinstitute.com